

# NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

## 60 V, 6.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- AEC-Q101 Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

| Rating                         | Symbol    | Max   | Unit |
|--------------------------------|-----------|-------|------|
| Collector-Emitter Voltage      | $V_{CEO}$ | -60   | Vdc  |
| Collector-Base Voltage         | $V_{CBO}$ | -100  | Vdc  |
| Emitter-Base Voltage           | $V_{EBO}$ | -6.0  | Vdc  |
| Collector Current - Continuous | $I_C$     | -6.0  | A    |
| Collector Current - Peak       | $I_{CM}$  | -12.0 | A    |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



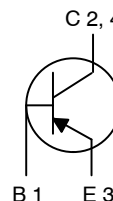
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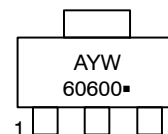
**-60 VOLTS, 6.0 AMPS  
2.0 WATTS  
PNP LOW  $V_{CE(sat)}$  TRANSISTOR  
EQUIVALENT  $R_{DS(on)}$  50 mΩ**



**SOT-223  
CASE 318E  
STYLE 1**

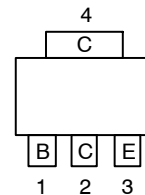


### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
60600 = Specific Device Code  
▪ = Pb-Free Package

### PIN ASSIGNMENT



Top View Pinout

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

## THERMAL CHARACTERISTICS

| Characteristic                                                                          | Symbol                           | Max         | Unit                       |
|-----------------------------------------------------------------------------------------|----------------------------------|-------------|----------------------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 1)                   | 800<br>6.5  | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction-to-Ambient                                              | $R_{\theta JA}$ (Note 1)         | 155         | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 2)                   | 2<br>15.6   | W<br>mW/ $^\circ\text{C}$  |
| Thermal Resistance,<br>Junction-to-Ambient                                              | $R_{\theta JA}$ (Note 2)         | 64          | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation<br>(Single Pulse < 10 sec.)                                    | $P_{D\text{single}}$<br>(Note 3) | 710         | mW                         |
| Junction and Storage Temperature Range                                                  | $T_J, T_{\text{stg}}$            | -55 to +150 | $^\circ\text{C}$           |

1. FR-4 @ 7.6 mm<sup>2</sup>, 1 oz. copper traces.
2. FR-4 @ 645 mm<sup>2</sup>, 1 oz. copper traces.
3. Thermal response.

## ORDERING INFORMATION

| Device         | Package              | Shipping <sup>†</sup> |
|----------------|----------------------|-----------------------|
| NSS60600MZ4T1G | SOT-223<br>(Pb-Free) | 1,000 / Tape & Reel   |
| NSV60600MZ4T1G | SOT-223<br>(Pb-Free) | 1,000 / Tape & Reel   |
| NSS60600MZ4T3G | SOT-223<br>(Pb-Free) | 4,000 / Tape & Reel   |
| NSV60600MZ4T3G | SOT-223<br>(Pb-Free) | 4,000 / Tape & Reel   |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                             |               |      |   |      |               |
|-----------------------------------------------------------------------------|---------------|------|---|------|---------------|
| Collector – Emitter Breakdown Voltage ( $I_C = -10\text{ mA}$ , $I_B = 0$ ) | $V_{(BR)CEO}$ | -60  | – | –    | Vdc           |
| Collector – Base Breakdown Voltage ( $I_C = -0.1\text{ mA}$ , $I_E = 0$ )   | $V_{(BR)CBO}$ | -100 | – | –    | Vdc           |
| Emitter – Base Breakdown Voltage ( $I_E = -0.1\text{ mA}$ , $I_C = 0$ )     | $V_{(BR)EBO}$ | -6.0 | – | –    | Vdc           |
| Collector Cutoff Current ( $V_{CB} = -100\text{ Vdc}$ , $I_E = 0$ )         | $I_{CBO}$     | –    | – | -0.1 | $\mu\text{A}$ |
| Emitter Cutoff Current ( $V_{EB} = -6.0\text{ Vdc}$ )                       | $I_{EBO}$     | –    | – | -0.1 | $\mu\text{A}$ |

### ON CHARACTERISTICS

|                                                                                                                                                                                                                                                                                                                               |               |                         |                                 |                                                |     |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-------------------------|---------------------------------|------------------------------------------------|-----|
| DC Current Gain (Note 4)<br>( $I_C = -500\text{ mA}$ , $V_{CE} = -2.0\text{ V}$ )<br>( $I_C = -1.0\text{ A}$ , $V_{CE} = -2.0\text{ V}$ )<br>( $I_C = -2.0\text{ A}$ , $V_{CE} = -2.0\text{ V}$ )<br>( $I_C = -6.0\text{ A}$ , $V_{CE} = -2.0\text{ V}$ )                                                                     | $h_{FE}$      | 150<br>120<br>100<br>70 | –<br>–<br>–<br>–                | –<br>360<br>–<br>–                             | –   |
| Collector – Emitter Saturation Voltage (Note 4)<br>( $I_C = -0.1\text{ A}$ , $I_B = -2.0\text{ mA}$ )<br>( $I_C = -1.0\text{ A}$ , $I_B = -0.100\text{ A}$ )<br>( $I_C = -2.0\text{ A}$ , $I_B = -0.200\text{ A}$ )<br>( $I_C = -3.0\text{ A}$ , $I_B = -60\text{ mA}$ )<br>( $I_C = -6.0\text{ A}$ , $I_B = -0.6\text{ A}$ ) | $V_{CE(sat)}$ | –<br>–<br>–<br>–<br>–   | –<br>-0.050<br>-0.100<br>–<br>– | -0.050<br>-0.070<br>-0.120<br>-0.250<br>-0.350 | V   |
| Base – Emitter Saturation Voltage (Note 4)<br>( $I_C = -1.0\text{ A}$ , $I_B = -0.1\text{ A}$ )                                                                                                                                                                                                                               | $V_{BE(sat)}$ | –                       | –                               | -1.0                                           | V   |
| Base – Emitter Turn-on Voltage (Note 4)<br>( $I_C = -1.0\text{ A}$ , $V_{CE} = -2.0\text{ V}$ )                                                                                                                                                                                                                               | $V_{BE(on)}$  | –                       | –                               | -0.900                                         | V   |
| Cutoff Frequency<br>( $I_C = -500\text{ mA}$ , $V_{CE} = -10\text{ V}$ , $f = 1.0\text{ MHz}$ )                                                                                                                                                                                                                               | $f_T$         | 100                     | –                               | –                                              | MHz |
| Input Capacitance ( $V_{EB} = 5.0\text{ V}$ , $f = 1.0\text{ MHz}$ )                                                                                                                                                                                                                                                          | $C_{ibo}$     | –                       | 360                             | –                                              | pF  |
| Output Capacitance ( $V_{CB} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )                                                                                                                                                                                                                                                          | $C_{obo}$     | –                       | 60                              | –                                              | pF  |

### SWITCHING CHARACTERISTICS

|                                                                                       |       |   |     |   |    |
|---------------------------------------------------------------------------------------|-------|---|-----|---|----|
| Delay ( $V_{CC} = -30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )   | $t_d$ | – | 100 | – | ns |
| Rise ( $V_{CC} = -30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )    | $t_r$ | – | 180 | – | ns |
| Storage ( $V_{CC} = -30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ ) | $t_s$ | – | 540 | – | ns |
| Fall ( $V_{CC} = -30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )    | $t_f$ | – | 145 | – | ns |

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .

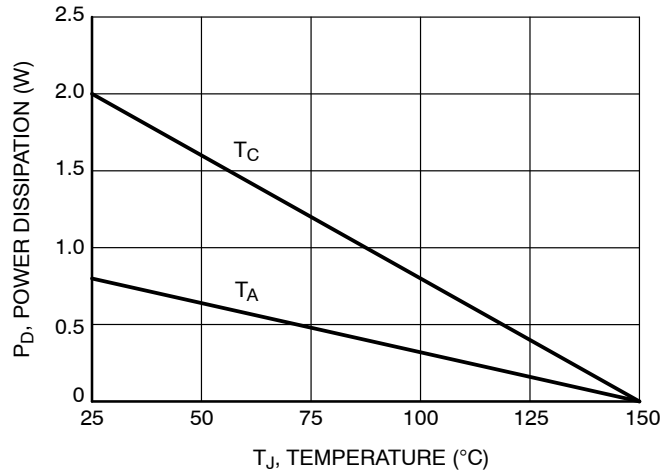


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

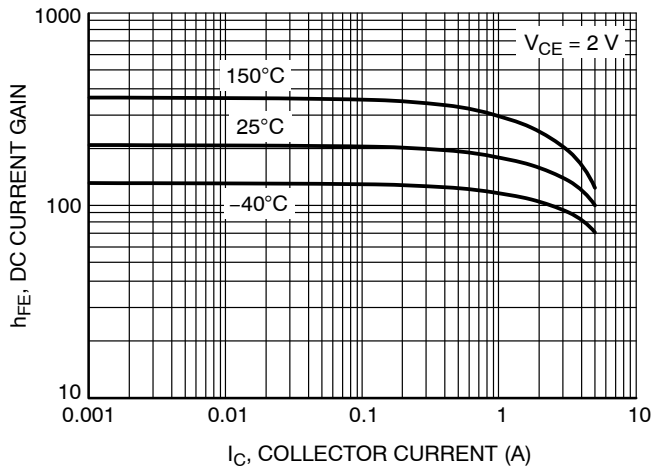


Figure 2. DC Current Gain

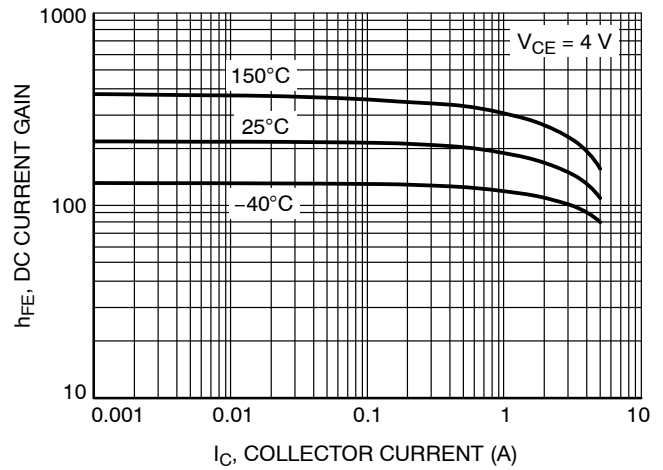


Figure 3. DC Current Gain

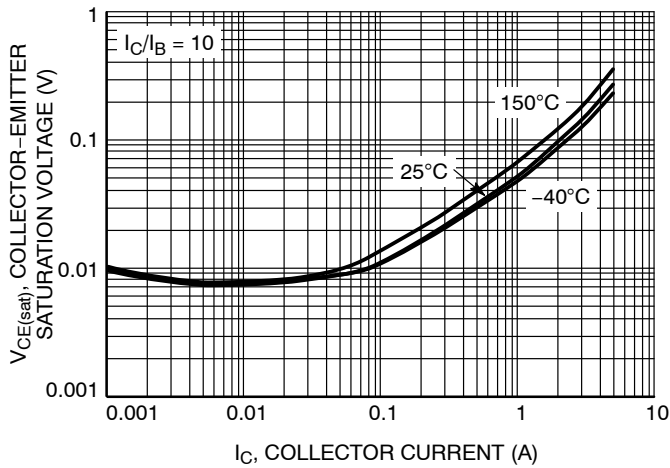


Figure 4. Collector-Emitter Saturation Voltage

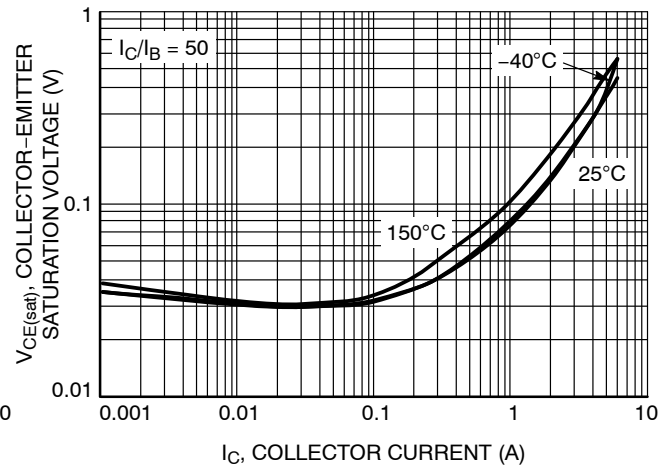


Figure 5. Collector-Emitter Saturation Voltage

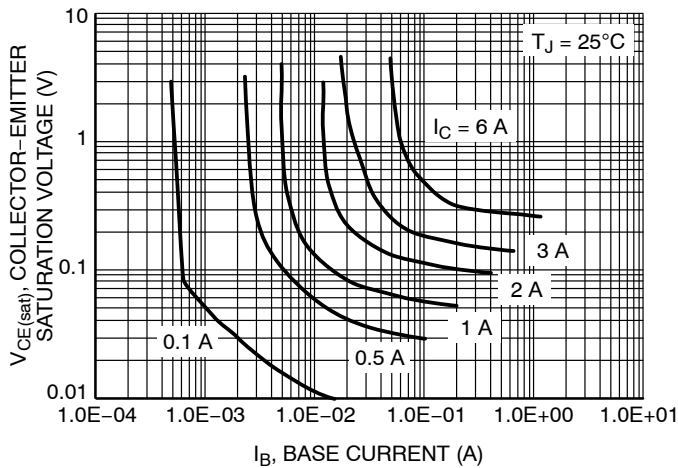


Figure 6. Collector Saturation Region

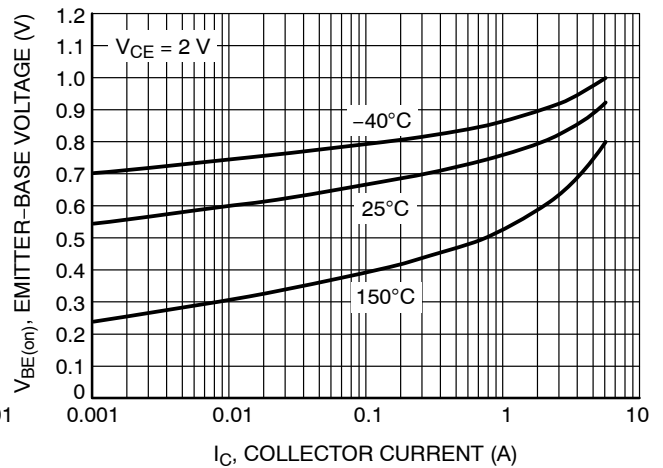


Figure 7.  $V_{BE(on)}$  Voltage

TYPICAL CHARACTERISTICS

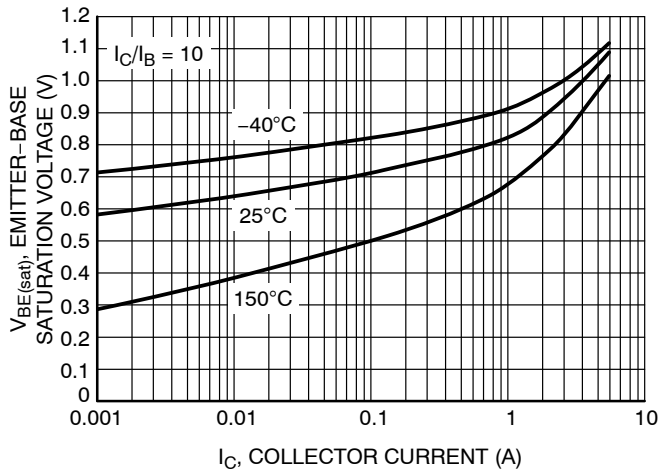


Figure 8. Base-Emitter Saturation Voltage

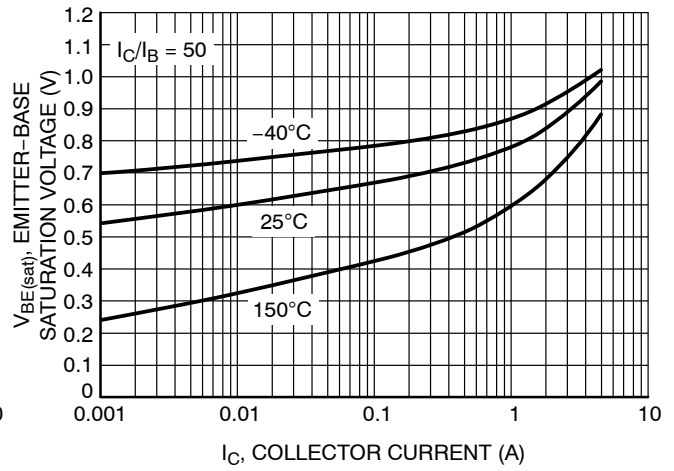


Figure 9. Base-Emitter Saturation Voltage

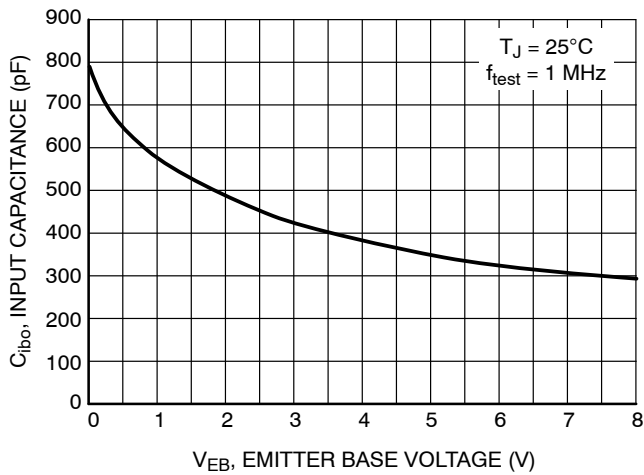


Figure 10. Input Capacitance

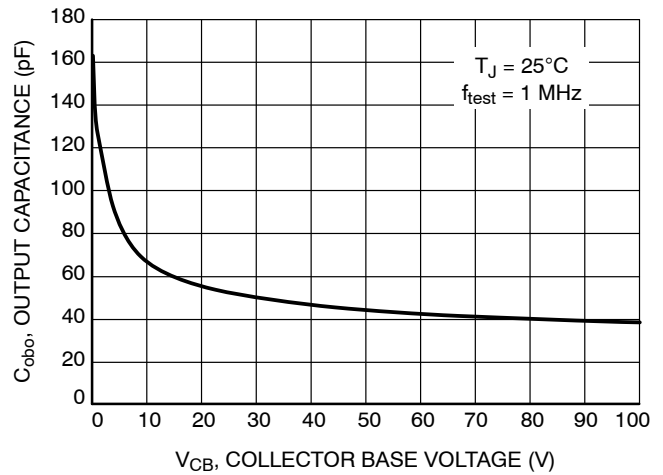


Figure 11. Output Capacitance

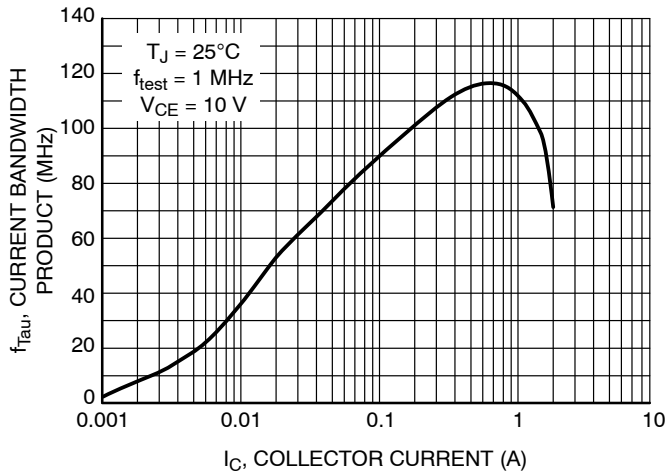


Figure 12. Current-Gain Bandwidth Product

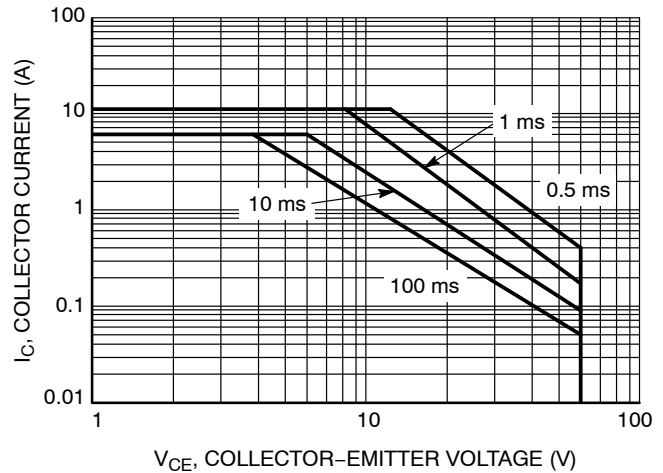
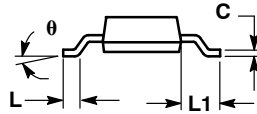
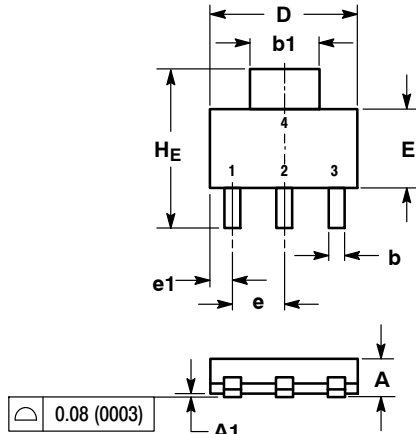


Figure 13. Safe Operating Area

# NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

## PACKAGE DIMENSIONS

### SOT-223 (TO-261) CASE 318E-04 ISSUE N

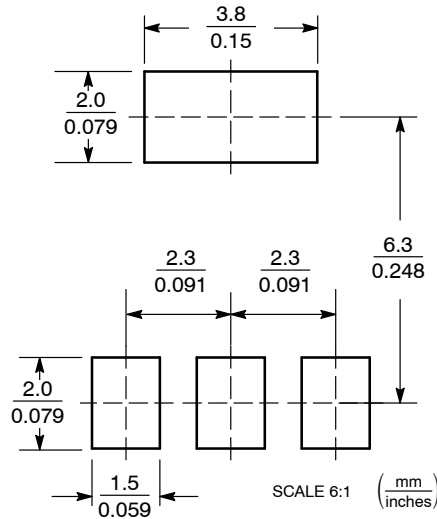


NOTES:  
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.  
2. CONTROLLING DIMENSION: INCH.

| DIM   | MILLIMETERS |      |      | INCHES |       |       |
|-------|-------------|------|------|--------|-------|-------|
|       | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A     | 1.50        | 1.63 | 1.75 | 0.060  | 0.064 | 0.068 |
| A1    | 0.02        | 0.06 | 0.10 | 0.001  | 0.002 | 0.004 |
| b     | 0.60        | 0.75 | 0.89 | 0.024  | 0.030 | 0.035 |
| b1    | 2.90        | 3.06 | 3.20 | 0.115  | 0.121 | 0.126 |
| c     | 0.24        | 0.29 | 0.35 | 0.009  | 0.012 | 0.014 |
| D     | 6.30        | 6.50 | 6.70 | 0.249  | 0.256 | 0.263 |
| E     | 3.30        | 3.50 | 3.70 | 0.130  | 0.138 | 0.145 |
| e     | 2.20        | 2.30 | 2.40 | 0.087  | 0.091 | 0.094 |
| e1    | 0.85        | 0.94 | 1.05 | 0.033  | 0.037 | 0.041 |
| L     | 0.20        | ---  | ---  | 0.008  | ---   | ---   |
| L1    | 1.50        | 1.75 | 2.00 | 0.060  | 0.069 | 0.078 |
| H_E   | 6.70        | 7.00 | 7.30 | 0.264  | 0.276 | 0.287 |
| theta | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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**NSS60600MZ4/D**



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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